

Title (en)

ELECTRONIC SEMICONDUCTOR COMPONENT, AND PROCESS FOR MANUFACTURING A PRETREATED COMPOSITE SUBSTRATE FOR AN ELECTRONIC SEMICONDUCTOR COMPONENT

Title (de)

ELEKTRONISCHES HALBLEITERBAUELEMENT UND VERFAHREN ZUR HERSTELLUNG EINES VORBEHANDELTEN VERBUNDSTRATS FÜR EIN ELEKTRONISCHES HALBLEITERBAUELEMENT

Title (fr)

COMPOSANT SEMI-CONDUCTEUR ÉLECTRONIQUE ET PROCÉDÉ DE FABRICATION D'UN SUBSTRAT COMPOSITE PRÉTRAITÉ POUR COMPOSANT SEMI-CONDUCTEUR ÉLECTRONIQUE

Publication

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Application

**EP 21836128 A 20211210**

Priority

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Abstract (en)

[origin: WO2022128818A1] The electronic semiconductor component (50) includes a crystal (53) made of monocrystalline SiC, wherein the orientation of at least some subareas of a first surface (58) of the SiC crystal (53) extends substantially in a direction running perpendicularly to the c direction (c) of the crystal structure of the crystal (53). Also disclosed is a manufacturing process.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

See references of WO 2022128818A1

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